

CMOS IMAGE SENSOR DEVICE AND METHOD

ABSTRACT

A photodiode device including a well located in a substrate, a floating node located in the well and shallow trench isolation (STI) regions located over and laterally opposing the floating node. A borderless contact buffer layer is located over at least the floating node, and an interlevel dielectric layer is located over the borderless contact buffer layer. A borderless contact extends through the interlevel dielectric layer and the borderless contact buffer layer to the floating node.